

1 ROBERT E. FREITAS (SBN 80948)
rfreitas@fawlaw.com
2 JASON S. ANGELL (SBN 221607)
jangell@fawlaw.com
3 JING H. CHERNG (SBN 265017)
gcherng@fawlaw.com
4 FREITAS ANGELL & WEINBERG LLP
350 Marine Parkway, Suite 200
5 Redwood Shores, California 94065
Telephone: (650) 593-6300
6 Facsimile: (650) 593-6301

7 Attorneys for Plaintiff
Polaris Innovations Ltd.

8

9

UNITED STATES DISTRICT COURT

10

NORTHERN DISTRICT OF CALIFORNIA

11

12

POLARIS INNOVATIONS LTD., an
Ireland limited company,

13

Plaintiff,

14

v.

15

INTEGRATED SILICON SOLUTION,
INC., a Delaware corporation,

16

17

Defendant.

18

19

20

21

22

23

24

25

26

27

28

No.

**COMPLAINT FOR PATENT
INFRINGEMENT**

DEMAND FOR JURY TRIAL

1 Polaris Innovations Limited (“Polaris”) files this Complaint against Integrated Silicon
2 Solution, Inc. (“ISSI”) for ISSI’s infringement of United States Patents 6,653,882 B2 and
3 6,728,143 B2. Polaris alleges as follows:

4 **PARTIES**

5 1. Polaris is a limited company organized and existing under the laws of the Republic
6 of Ireland, with its principal place of business at 29 Earlsfort Terrace, Dublin 2, Republic of
7 Ireland.

8 2. ISSI is a corporation organized and existing under the laws of the State of
9 Delaware, with its principal place of business at 1623 Buckeye Dr., Milpitas, CA 95035.

10 **JURISDICTION**

11 3. Polaris brings this action under the patent laws of the United States, 35 U.S.C. § 1
12 *et. seq.* This Court has subject matter jurisdiction over this action under 28 U.S.C. §§ 1331,
13 1332(a)(2), and 1338(a).

14 **VENUE**

15 4. ISSI has sold, offered to sell, and used in this District products that practice or
16 embody one or more claims of each of the patents in suit, as discussed more fully herein. ISSI’s
17 website describes its headquarters in this District as one of the “sales offices” from which it sells
18 computer memory products, including DDR3 synchronous dynamic random access memory
19 (“SDRAM”), which infringes the patents in suit. ISSI’s headquarters location in Milpitas,
20 California is a regular and established place of business in this District. Venue is proper in this
21 District under 28 U.S.C. § 1400(b).

22 **INTRADISTRICT ASSIGNMENT**

23 5. This is an Intellectual Property Action pursuant to Local Rule 3-2(c).

24 **THE PATENTS IN SUIT**

25 6. On November 25, 2003, the United States Patent and Trademark Office duly and
26 legally issued United States Patent No. 6,653,882 B2 (“’882 Patent”), which is entitled “Output
27 Drivers for IC,” and identifies Arindam Raychaudhuri as the sole inventor. A true and correct
28 copy of the ’882 Patent is attached hereto as Exhibit A. The ’882 Patent has been assigned to

1 Plaintiff Polaris. Polaris holds all right, title, and interest in the '882 Patent, including the right to
2 collect and receive damages for past, present and future infringement of the '882 Patent.

3 7. On April 27, 2004 the United States Patent and Trademark Office duly and legally
4 issued United States Patent No. 6,728,143 B2 ("the '143 Patent"), which is entitled "Integrated
5 Memory," and identifies Robert Feurle as the sole inventor. A true and correct copy of the '143
6 Patent is attached hereto as Exhibit B. The '143 Patent has been assigned to Plaintiff Polaris.
7 Polaris holds all right, title, and interest in the '143 Patent, including the right to collect and
8 receive damages for past, present and future infringement of the '143 Patent.

9 8. The '882 Patent discloses inventions related to integrated circuit devices including,
10 for example, SDRAM devices used in personal computer systems, among other products. The
11 inventions of the '882 Patent generally are directed to a novel output driver circuit that improves
12 data transfer speeds from an integrated circuit to other circuits in a computer system. The '143
13 Patent discloses inventions related to integrated memory devices such as SDRAM that can be
14 used in personal computer systems and other products. The inventions of the '143 Patent
15 generally are directed to improving memory access times, and thus the operating speed of a
16 memory device, by employing a novel control circuit for performing memory accesses.

17 9. The usefulness and value of the patents in suit has been acknowledged by various
18 companies engaged in the design, manufacture, and sale of SDRAM devices. Polaris has widely
19 licensed the patents in suit to numerous SDRAM manufacturers, among others, some of which
20 compete with ISSI for sales of SDRAM devices.

21 10. Polaris has offered to license the patents in suit to ISSI. Polaris has engaged in
22 numerous discussions with ISSI, through correspondence and in person and telephonic meetings
23 spanning several months, but ISSI has not agreed to license the patents in suit despite several
24 good-faith offers from Polaris. Polaris has therefore been compelled to file this suit to protect its
25 rights.

26 **FIRST CLAIM FOR RELIEF**

27 **Infringement of U.S. Patent No. 6,653,882**

28 11. Polaris realleges and incorporates by reference the allegations of paragraphs 1-10,

1 inclusive, as if set forth in full herein.

2 12. ISSI has infringed, and continues to infringe, at least claims 1 and 4 of the '882
3 Patent. ISSI uses, sells, or offers to sell in the United States, products, such as DDR3 SDRAM,
4 including IS43/46TR16256, IS43/46TR85120 512Mx8, 256Mx16 4Gb DDR3 SDRAM ("ISSI
5 DDR3 SDRAM"), that meet each and every limitation of claim 1.

6 13. Claim 1 of the '882 Patent is directed to an output driver for an integrated circuit.
7 The output driver comprises:

- 8 a. a driver circuit for driving an external circuit, the driver circuit having:
- 9 i. a data input connected to the integrated circuit;
 - 10 ii. a data output connected to a transmission line leading to the
11 external circuit;
 - 12 iii. and an impedance adjusting means for adjusting the output
13 impedance of the driver circuit according to impedance adjusting data;
- 14 b. a dummy circuit comprising a dummy driver circuit and a dummy
15 transmission line, the dummy driver circuit and the dummy transmission line being
16 electrical replicas of the driver circuit and the transmission line, respectively;
- 17 c. and an impedance control circuit for controlling the output impedance of
18 the driver circuit, the impedance control circuit being connected to the dummy
19 circuit and the impedance adjusting means,
- 20 i. wherein the impedance control circuit is configured to
21 control the impedance of the driver circuit by determining the
22 impedance adjusting data necessary for matching the output impedance
23 of the dummy driver circuit to the impedance of the dummy
24 transmission line and outputting the determined impedance adjusting
25 data to the impedance adjusting means of the driver circuit, wherein the
26 dummy driver circuit is a scaled down replica of the driver circuit.

27 14. The ISSI DDR3 SDRAM meets each and every limitation of claim 1. For
28 example, the ISSI DDR3 SDRAM is an integrated circuit that contains an output driver for

1 driving an external circuit. The output driver of the ISSI DDR3 SDRAM includes a driver circuit
 2 having a data input connected to the integrated circuit and a data output connected to a
 3 transmission line leading to the external circuit. For example, the ISSI DDR3 SDRAM contains a
 4 DQ (DQL, DQU) pinout of the bi-directional data bus. *See, e.g.* [http://www.issi.com/WW/pdf/43-](http://www.issi.com/WW/pdf/43-46TR16256A-85120AL.pdf)
 5 [46TR16256A-85120AL.pdf](http://www.issi.com/WW/pdf/43-46TR16256A-85120AL.pdf) (“ISSI Datasheet”) at 4, 42.

6 15. The ISSI DDR3 SDRAM is capable of adjusting the output impedance of the
 7 driver circuit, and does so through an impedance adjusting means for adjusting the output
 8 impedance of the driver circuit according to impedance adjusting data. For example, the ISSI
 9 Datasheet describes ZQ Calibration, a way of adjusting the output impedance of the driver circuit.
 10 *See, e.g.*, ISSI Datasheet at 6, 13, 14, 42. The ISSI DDR3 SDRAM also contains a dummy circuit
 11 comprising a dummy driver circuit and a dummy transmission line, the dummy driver circuit and
 12 the dummy transmission line being electrical replicas of the driver circuit and the transmission
 13 line, respectively. The dummy circuit is indicated in the ISSI Datasheet as, for example, the ZQ
 14 pin and the RZQ reference resistor. *See, e.g.*, ISSI Datasheet at 1, 5.

15 16. The ISSI DDR3 SDRAM also contains an impedance control circuit for
 16 controlling the output impedance of the driver circuit, the impedance control circuit being
 17 connected to the dummy circuit and the impedance adjusting means. *See, e.g.*, ISSI Datasheet at
 18 13:

A5	A1	Output Driver Impedance Control
0	0	RZQ/6
0	1	RZQ/7
1	0	Reserved
1	1	Reserved

19
 20
 21
 22 17. The ISSI DDR3 SDRAM’s use of ZQ Calibration indicates that the impedance
 23 control circuit of the ISSI DDR3 SDRAM is configured to control the impedance of the driver
 24 circuit by determining the impedance adjusting data necessary for matching the output impedance
 25 of the dummy driver circuit to the impedance of the dummy transmission line and outputting the
 26 determined impedance adjusting data to the impedance adjusting means of the driver circuit. The
 27 dummy driver circuit is a scaled down replica of the driver circuit, as shown by the RZQ/6 and
 28 RZQ/7 values in the table appearing on page 13 of the ISSI Datasheet.

1 18. Claim 4 of the '882 patent depends on claim 1, and claims "The output driver
2 according to claim 1, wherein the driver circuit is a push-pull on-chip current driver."

3 19. The driver circuit of the ISSI DDR3 SDRAM is a push-pull on-chip current driver,
4 as seen in Fig. 5.7 of the ISSI Datasheet:

5 **5.7 340hm Output Driver DC Electrical Characteristics**

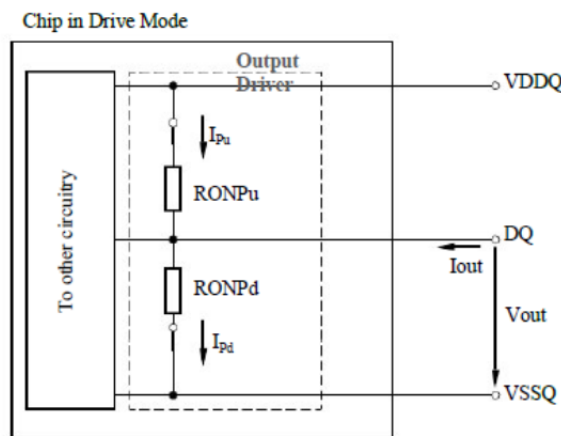
6 A Functional representation of the output buffer is shown as below. Output driver impedance RON is defined by the value
of the external reference resistor RZQ as follows:

7 $R_{ON34} = R_{ZQ} / 7$ (nominal 34.4ohms +/-10% with nominal RZQ=240ohms)

The individual pull-up and pull-down resistors (R_{ONPu} and R_{ONPd}) are defined as follows:

8 $R_{ONPu} = [V_{DDQ} - V_{out}] / |I_{out}|$ ----- under the condition that R_{ONPd} is turned off (1)

$R_{ONPd} = V_{out} / |I_{out}|$ ----- under the condition that R_{ONPu} is turned off (2)



10
11
12
13
14
15
16 **Figure 5.7 Output Driver : Definition of Voltages and Currents**

17 20. Upon information and belief, other ISSI products similarly infringe one or more
18 claims of the '882 Patent. The specific part numbers of all ISSI products that practice one or
19 more claims of the '882 Patent are not presently known to Polaris. Polaris accuses of
20 infringement all ISSI products that contain features and functions similar to those described above
21 that practice one or more claims of the '882 Patent.

22 21. ISSI has had notice of the '882 Patent and of its infringement of the '882 Patent
23 for more than one year. Before initiating litigation, Polaris made substantial efforts to license
24 ISSI's use of the inventions claimed in the '882 Patent, expecting that ISSI would engage in good
25 faith licensing discussions. ISSI has refused to license the '882 Patent, and it continues to infringe
26 one or more claims of the '882 Patent despite being aware of its infringement of the '882 Patent
27 on the basis of claim charts provided by Polaris. ISSI's infringement of the '882 Patent has
28 therefore been, and continues to be, willful, deliberate, and egregious, and has caused and

1 continues to cause substantial damage to Polaris.

2 **SECOND CLAIM FOR RELIEF**

3 **Infringement of U.S. Patent No. 6,728,143**

4 22. Polaris realleges and incorporates by reference the allegations of paragraphs 1-10,
5 inclusive, as if set forth in full herein.

6 23. ISSI has infringed, and continues to infringe, at least claims 1 and 2 of the '143
7 patent. ISSI uses, sells, or offers to sell in the United States, products, such as DDR3 SDRAM,
8 including IS43/46TR16256, IS43/46TR85120 512Mx8, 256Mx16 4Gb DDR3 SDRAM, that meet
9 each and every limitation of claim 1.

10 24. Claim 1 of the '143 Patent is directed to an integrated memory. The integrated
11 memory comprises:

12 a. a memory cell array having memory cells;

13 b. a control circuit for controlling a memory access selected from the group
14 consisting of a read memory access for reading out a data signal from one of said
15 memory cells and a write memory access for writing a data signal into one of said
16 memory cells;

17 c. for performing the memory access, said control circuit designed for
18 receiving an access command selected from the group consisting of an activation
19 command, a read command, and a write command;

20 d. for performing the memory access, said control circuit designed for
21 receiving a configuration value in a combined manner with the access command;
22 and

23 e. the configuration value being selected from the group consisting of a CAS
24 latency value and a value for specifying a burst access.

25 25. ISSI DDR3 SDRAM contains a memory cell array having memory cells. For
26 example, the datasheet for the ISSI DDR3 SDRAM describes "8 internal banks for concurrent
27 operation." *See e.g.*, ISSI Datasheet at 1. The ISSI DDR3 SDRAM contains a control circuit for
28 controlling read and write memory accesses. For example, the control circuit uses a command

1 truth table as described on page 20 of the ISSI Datasheet. The control circuit of the ISSI DDR3
 2 SDRAM is designed to receive access commands in the form of activation commands, read
 3 commands (e.g., RDS4, RDS8), and write commands (e.g., WRS4, WRS8). *See* ISSI Datasheet,
 4 p.20. The control circuit is further designed to receive a configuration value in a combined
 5 manner with the access command, e.g., A12/BC# values in the command truth table. *See* ISSI
 6 Datasheet, p.20. The configuration value received by the ISSI DDR3 SDRAM is, for example, a
 7 value for specifying a burst access. *See, e.g.,* ISSI Datasheet at 4:

A12 / BC#	Input	Burst Chop: A12 / BC# is sampled during Read and Write commands to determine if burst chop (on-the-fly) will be performed. (HIGH, no burst chop; LOW: burst chopped). See command truth table for details.
-----------	-------	--

10 26. Claim 2 of the '143 Patent is dependent upon Claim 1, and claims "The integrated
 11 memory according to claim 1, wherein: said control circuit is designed to receive a multi-bit
 12 signal that includes the access command and the configuration value."

13 27. The control circuit of the ISSI DDR3 SDRAM is designed to receive a multi-bit
 14 signal that includes the access command and the configuration value, including bits for CS#,
 15 RAS#, CAS#, WE#, BA0-BA2, A11 A13 A14 A15, A12/BC#, A10/AP, and A0-A9. *See* ISSI
 16 Datasheet, p.20.

17 28. Upon information and belief, other ISSI products similarly infringe one or more
 18 claims of the '143 Patent. The specific part numbers of all ISSI products that practice one or
 19 more claims of the '143 Patent are not presently known to Polaris. Polaris accuses of
 20 infringement all ISSI products that contain features and functions similar to those described above
 21 that practice one or more claims of the '143 Patent.

22 29. ISSI has had notice of the '143 Patent and of its infringement of the '143 Patent
 23 for more than one year. Before initiating litigation, Polaris made substantial efforts to license
 24 ISSI's use of the inventions claimed in the '143 Patent, expecting that ISSI would engage in good
 25 faith licensing discussions. ISSI has refused to license the '143 Patent, and it continues to infringe
 26 one or more claims of the '143 Patent despite being aware of its infringement of the '143 Patent
 27 on the basis of claim charts provided by Polaris. ISSI's infringement of the '143 Patent has
 28 therefore been, and continues to be, willful, deliberate, and egregious, and has caused and

1 continues to cause substantial damage to Polaris.

2 WHEREFORE, Polaris prays that judgment be entered in its favor and against ISSI as
3 follows:

4 a. For damages in an amount according to proof, but no less than a reasonable royalty
5 for infringement of the patents in suit;

6 b. For enhanced damages pursuant to 35 U.S.C. § 284;

7 c. For prejudgment and post-judgment interest as provided by law;

8 d. For costs of suit and reasonable attorneys' fees incurred herein; and

9 e. For such other relief as the Court deems proper.

10 Dated: October 11, 2017

ROBERT E. FREITAS
JASON S. ANGELL
JING H. CHERNG
FREITAS ANGELL & WEINBERG LLP

13 /s/Jing Hong Cherng
14 Jing Hong Cherng
15 Attorneys for Plaintiff
16 Polaris Innovations Ltd.

17
18
19
20
21
22
23
24
25
26
27
28

1
2
3
4
5
6
7
8
9
10
11
12
13
14
15
16
17
18
19
20
21
22
23
24
25
26
27
28

DEMAND FOR JURY TRIAL

Pursuant to Rule 38 of the Federal Rules of Civil Procedure, Polaris demands a trial by jury on all issues so triable.

Dated: October 11, 2017

ROBERT E. FREITAS
JASON S. ANGELL
JING H. CHERNG
FREITAS ANGELL & WEINBERG LLP

/s/Jing Hong Cherng
Jing Hong Cherng
Attorneys for Plaintiff
Polaris Innovations Ltd.